

PIN photodiode amplifier C4890

Wide bandwidth amplifier (1.5 GHz, 20 dB)



C4890 wide-band amplifier, when connected to a high-speed PIN photodiode (S5791, S5972, S5973, etc.) converts optical signals at a maximum of 1.5 GHz into voltage outputs with exceptionally low distortion and 20 dB gain.

C4890 can also be combined with other types of PIN photodiodes and APDs (avalanche photodiodes) to serve as a high-frequency amplifier for optical measurements in a wide range of fields including industry and research applications.

Features

- Wide bandwidth, high gain, flat gain spectrum
- Flat, low group delay characteristics and low noise
- Input/output impedance: 50 Ω
- Small size, light weight, low price
- Single power supply operation (+12 V)

Applications

- High frequency amplifier for measurement
- PIN photodiode evaluation

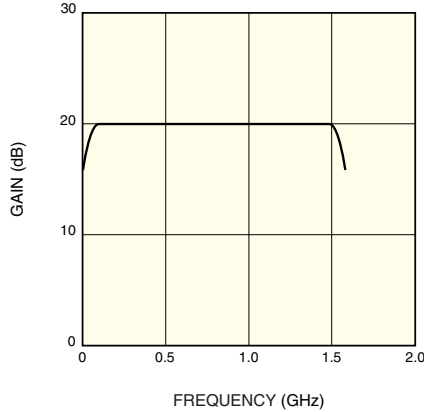
■ Absolute maximum ratings

Parameter	Condition	Value	Unit
Supply voltage		+13.5	V
Input voltage	Continuation RF input	+15	dBm
	DC	+1.25	V
Operating temperature		0 to +60	°C
Storage temperature		-10 to +70	°C

■ Electrical characteristics (Ta=25 °C, Vcc=12 V, Input/output is terminated with 50 Ω load.)

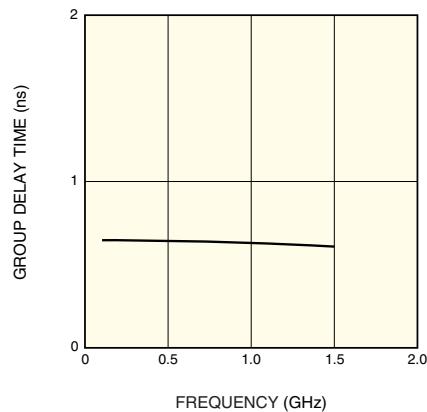
Parameter	Condition	Min.	Typ.	Max.	Unit
Cut-off frequency (-3 dB)	High band	1.0	1.5	-	GHz
	Low band	-	5	10	MHz
Gain	f=1.0 GHz	18	20	-	dB
Gain deviation within bandwidth	f=10 MHz to 1.0 GHz	-	± 1.0	-	dB
Group delay time		-	700	-	ps
VSWR	Input	-	1.1	-	dB
	Output	-	1.5	-	dB
1 dB compression point		-	7	-	dBm
Rise time		-	240	-	ps
Noise figure		-	8	-	dB
Current consumption		-	45	-	mA

■ Gain vs. frequency



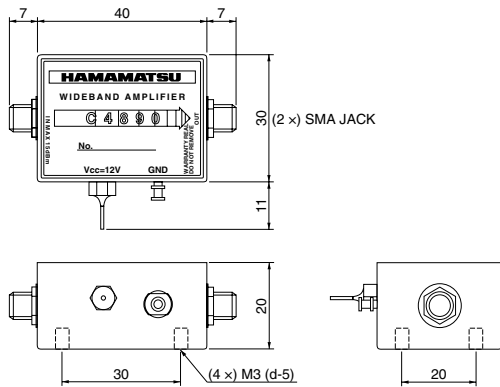
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■ Group delay time vs. frequency



KACCB0039EA

■ Dimensional outline (unit: mm)



KACCA0034EA

■ Application example: High-speed O/E converter module

A high-sensitivity O/E converter can be easily configured by using C4890 in conjunction with a high-speed PIN photodiode (S5973, etc). The following is an example when C4890 is used with S5973 to amplify the output signal after receiving an attenuator. Major performance items are shown below.

Effective bandwidth: 5 MHz to 1.5 GHz

The lower limit is determined by the amplifier (C4890) and the upper limit by the photodiode.

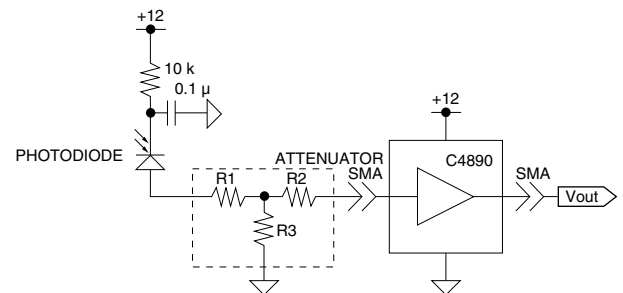
Conversion sensitivity (V/W) = $0.5 \text{ A/W} \times 50 \times (100 - \alpha)/100 \times 10 (\lambda=850 \text{ nm})$

$\uparrow$ Photodiode photoelectric sensitivity
 $\uparrow$ Attenuator input impedance
 $\uparrow$ Attenuator damp rate
 $\uparrow$ C4890 gain

Detection limit: 4.4 μWrms ($\lambda=850 \text{ nm}$, BW=1.5 GHz)

Depends on the amplifier NF (NF=8 dB Typ.).

■ Connection example



Resistance value according to the attenuator damp quantity

Damp quantity (dB)	Damp rate (%)	R1, R2 (Ω)	R3 (Ω)
0	0	0	50
3	30	8.2	150
6	50	16	68
10	70	27	36

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The above specifications are typical values and not guaranteed.

HAMAMATSU

HAMAMATSU PHOTONICS K.K., Solid State Division

1126-1 Ichino-cho, Hamamatsu City, 435-8558 Japan, Telephone: (81) 053-434-3311, Fax: (81) 053-434-5184, <http://www.hamamatsu.com>

U.S.A.: Hamamatsu Corporation, 360 Foothill Road, P.O.Box 6910, Bridgewater, N.J. 08807-0910, U.S.A., Telephone: (1) 908-231-0960, Fax: (1) 908-231-1218

Germany: Hamamatsu Photonics Deutschland GmbH, Arzbergerstr. 10, D-82211 Herrsching am Ammersee, Germany, Telephone: (49) 08152-3750, Fax: (49) 08152-2658

France: Hamamatsu Photonics France S.A.R.L.: 8, Rue du Saule Trappu, Parc du Moulin de Massy, 91882 Massy Cedex, France, Telephone: 33-(1) 69 53 71 00, Fax: 33-(1) 69 53 71 10

United Kingdom: Hamamatsu Photonics UK Limited: 2 Howard Court, 10 Tewin Road, Welwyn Garden City, Hertfordshire AL7 1BW, United Kingdom, Telephone: (44) 1707-294888, Fax: (44) 1707-325777

North Europe: Hamamatsu Photonics Norden AB: Smidesvägen 12, SE-171 41 Solna, Sweden, Telephone: (46) 8-509-031-00, Fax: (46) 8-509-031-01

Italy: Hamamatsu Photonics Italia S.R.L.: Strada della Moia, 1/E, 20020 Arese, (Milano), Italy, Telephone: (39) 02-935-81-733, Fax: (39) 02-935-81-741

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